

PMN30UNEX Datasheet

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DiGi Electronics Part Number PMN30UNEX-DG

Manufacturer Nexperia USA Inc.

Manufacturer Product Number PMN30UNEX

Description MOSFET N-CH 20V 4.8A 6TSOP

Detailed Description N-Channel 20 V 4.8A (Ta) 530mW (Ta), 4.46W (Tc) S

urface Mount 6-TSOP



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Purchase and inquiry

Manufacturer Product Number:	Manufacturer:
PMN30UNEX	Nexperia USA Inc.
Series:	Product Status:
-	Active
FET Type:	Technology:
N-Channel	MOSFET (Metal Oxide)
Drain to Source Voltage (Vdss):	Current - Continuous Drain (Id) @ 25°C:
20 V	4.8A (Ta)
Drive Voltage (Max Rds On, Min Rds On):	Rds On (Max) @ Id, Vgs:
1.5V, 4.5V	36mOhm @ 4.8A, 4.5V
Vgs(th) (Max) @ Id:	Gate Charge (Qg) (Max) @ Vgs:
900mV @ 250μA	9 nC @ 4.5 V
Vgs (Max):	Input Capacitance (Ciss) (Max) @ Vds:
±8V	558 pF @ 10 V
FET Feature:	Power Dissipation (Max):
	530mW (Ta), 4.46W (Tc)
Operating Temperature:	Mounting Type:
-55°C ~ 150°C (TJ)	Surface Mount
Supplier Device Package:	Package / Case:
6-TSOP	SC-74, SOT-457
Base Product Number:	
PMN30	

Environmental & Export classification

8541.29.0095

RoHS Status:	Moisture Sensitivity Level (MSL):
ROHS3 Compliant	1 (Unlimited)
REACH Status:	ECCN:
REACH Unaffected	EAR99
HTSUS:	



PMN30UNE

20 V, N-channel Trench MOSFET

29 January 2016

Product data sheet

1. General description

N-channel enhancement mode Field-Effect Transistor (FET) in a small SOT457 (SC-74) Surface-Mounted Device (SMD) plastic package using Trench MOSFET technology.

2. Features and benefits

- Trench MOSFET technology
- Low threshold voltage
- Very fast switching
- Enhanced power dissipation capability of 1240 mW
- ElectroStatic Discharge (ESD) protection > 1 kV HBM

3. Applications

- LED driver
- Power management
- Low-side loadswitch
- Switching circuits

4. Quick reference data

Table 1. Quick reference data

Symbol	Parameter	Conditions		Min	Тур	Max	Unit
V _{DS}	drain-source voltage	T _j = 25 °C		-	-	20	V
V_{GS}	gate-source voltage			-8	-	8	V
I _D	drain current	V _{GS} = 4.5 V; T _{amb} = 25 °C; t ≤ 5 s	[1]	-	-	6	Α
Static characte	Static characteristics						,
R _{DSon}	drain-source on-state resistance	$V_{GS} = 4.5 \text{ V}; I_D = 4.8 \text{ A}; T_j = 25 \text{ °C}$		-	28	36	mΩ

^[1] Device mounted on an FR4 PCB, single-sided copper, tin-plated, mounting pad for drain 6 cm².



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5. Pinning information

Table 2. Pinning information

Pin	Symbol	Description	Simplified outline	Graphic symbol
1	D	drain	<u> </u>	D I
2	D	drain		
3	G	gate	1 12 13	G T
4	S	source	TSOP6 (SOT457)	
5	D	drain		
6	D	drain		S 017aaa255

6. Ordering information

Table 3. Ordering information

Type number	Package			
	Name	Description	Version	
PMN30UNE	TSOP6	plastic surface-mounted package (TSOP6); 6 leads	SOT457	

7. Marking

Table 4. Marking codes

Type number	Marking code
PMN30UNE	G8

8. Limiting values

Table 5. Limiting values

In accordance with the Absolute Maximum Rating System (IEC 60134).

Symbol	Parameter	Conditions		Min	Max	Unit	
V _{DS}	drain-source voltage	T _j = 25 °C		-	20	V	
V_{GS}	gate-source voltage			-8	8	V	
I _D	drain current	$V_{GS} = 4.5 \text{ V}; T_{amb} = 25 ^{\circ}\text{C}; t \le 5 \text{ s}$	[1]	-	6	Α	
		V_{GS} = 4.5 V; T_{amb} = 25 °C	[1]	-	4.8	Α	
		V _{GS} = 4.5 V; T _{amb} = 100 °C	[1]	-	3	Α	
I _{DM}	peak drain current	T_{amb} = 25 °C; single pulse; $t_p \le 10 \mu s$		-	19	Α	
P _{tot}	total power dissipation	T _{amb} = 25 °C	[2]	-	530	mW	
			[1]	-	1.24	W	
		T _{sp} = 25 °C		-	4.46	W	
Tj	junction temperature			-55	150	°C	
T _{amb}	ambient temperature			-55	150	°C	
T _{stg}	storage temperature			-65	150	°C	
Source-dra	Source-drain diode						
Is	source current	T _{amb} = 25 °C	[1]	-	1.2	Α	

- Device mounted on an FR4 PCB, single-sided copper, tin-plated, mounting pad for drain 6 cm².
- [2] Device mounted on an FR4 Printed-Circuit Board (PCB), single-sided copper, tin-plated and standard footprint.

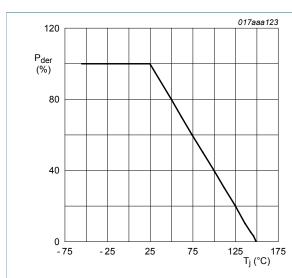


Fig. 1. Normalized total power dissipation as a function of junction temperature

$$P_{der} = \frac{P_{tot}}{P_{tot(25^{\circ}C)}} \times 100 \%$$

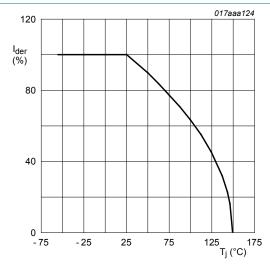


Fig. 2. Normalized continuous drain current as a function of junction temperature

$$I_{der} = \frac{I_D}{I_{D(25^{\circ}C)}} \times 100 \%$$

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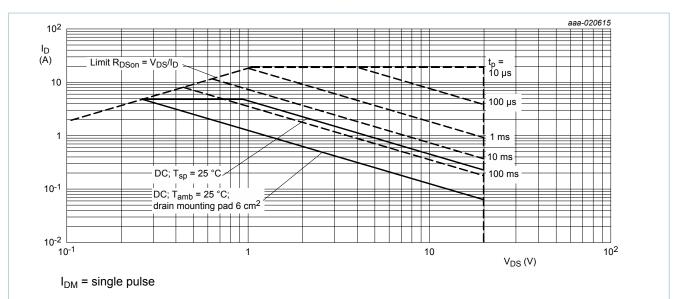


Fig. 3. Safe operating area; junction to ambient; continuous and peak drain currents as a function of drain-source voltage

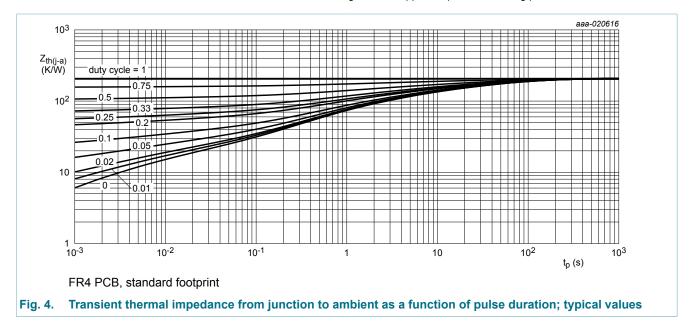
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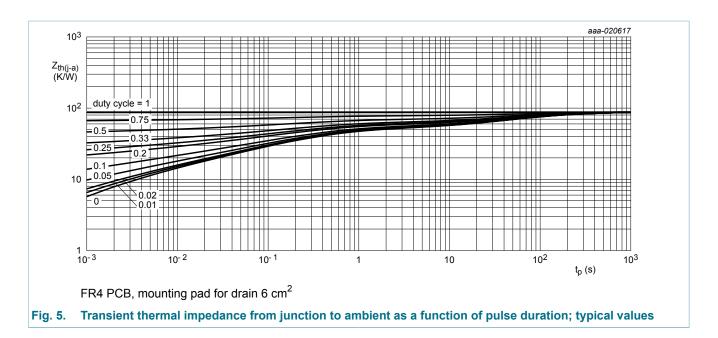
9. Thermal characteristics

Table 6. Thermal characteristics

Symbol	Parameter	Conditions		Min	Тур	Max	Unit
R _{th(j-a)} thermal resistance	in free air	[1]	-	205	235	K/W	
	from junction to ambient		[2]	-	88	101	K/W
ambient		in free air; t ≤ 5 s	[2]	-	55	63	K/W
R _{th(j-sp)}	thermal resistance from junction to solder point			-	24	28	K/W

- [1] Device mounted on an FR4 PCB, single-sided copper, tin-plated and standard footprint.
- [2] Device mounted on an FR4 PCB, single-sided copper, tin-plated, mounting pad for drain 6 cm².





20 V, N-channel Trench MOSFET

10. Characteristics

Table 7. Characteristics

Symbol	Parameter	Conditions	Min	Тур	Max	Unit
Static char	acteristics		,			
$V_{(BR)DSS}$	drain-source breakdown voltage	$I_D = 250 \mu A; V_{GS} = 0 V; T_j = 25 °C$	20	-	-	V
V_{GSth}	gate-source threshold voltage	$I_D = 250 \mu A; V_{DS} = V_{GS}; T_j = 25 \text{ °C}$	0.4	0.65	0.9	V
I _{DSS}	drain leakage current	V _{DS} = 20 V; V _{GS} = 0 V; T _j = 25 °C	-	-	1	μA
I _{GSS}	gate leakage current	V _{GS} = 8 V; V _{DS} = 0 V; T _j = 25 °C	-	-	10	μA
		V _{GS} = -8 V; V _{DS} = 0 V; T _j = 25 °C	-	-	-10	μA
		V _{GS} = 4.5 V; V _{DS} = 0 V; T _j = 25 °C	-	-	2	μA
		V _{GS} = -4.5 V; V _{DS} = 0 V; T _j = 25 °C	-	-	-2	μA
		V _{GS} = 2.5 V; V _{DS} = 0 V; T _j = 25 °C	-	-	200	nA
		V _{GS} = -2.5 V; V _{DS} = 0 V; T _j = 25 °C	-	-	-200	nA
R _{DSon}	drain-source on-state	V _{GS} = 4.5 V; I _D = 4.8 A; T _j = 25 °C	-	28	36	mΩ
	resistance	V _{GS} = 4.5 V; I _D = 4.8 A; T _j = 150 °C	-	43	55	mΩ
		V _{GS} = 2.5 V; I _D = 4.2 A; T _j = 25 °C	-	38	47	mΩ
		V _{GS} = 1.8 V; I _D = 0.9 A; T _j = 25 °C	-	42	60	mΩ
		V _{GS} = 1.5 V; I _D = 0.1 A; T _j = 25 °C	-	52	105	mΩ
9 _{fs}	forward transconductance	V_{DS} = 10 V; I_D = 5 A; T_j = 25 °C	-	19	-	S
R _G	gate resistance	f = 1 MHz; T _j = 25 °C	-	0.8	-	Ω
Dynamic cl	haracteristics		1			
Q _{G(tot)}	total gate charge	V _{DS} = 10 V; I _D = 4.8 A; V _{GS} = 4.5 V;	-	5.1	9	nC
Q_{GS}	gate-source charge	T _j = 25 °C	-	0.6	-	nC
Q_{GD}	gate-drain charge		-	0.9	-	nC
C _{iss}	input capacitance	V _{DS} = 10 V; f = 1 MHz; V _{GS} = 0 V;	-	558	-	pF
C _{oss}	output capacitance	$T_j = 25 ^{\circ}\text{C}$	-	56	-	pF
C _{rss}	reverse transfer capacitance		-	45	-	pF
t _{d(on)}	turn-on delay time	V _{DS} = 10 V; I _D = 4.8 A; V _{GS} = 4.5 V;	-	5.5	-	ns
t _r	rise time	$R_{G(ext)} = 6 \Omega; T_j = 25 °C$	-	24	-	ns
t _{d(off)}	turn-off delay time		-	22	-	ns
t _f	fall time		-	6	-	ns

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Symbol	Parameter	Conditions		Min	Тур	Max	Unit
Source-drain o	Source-drain diode						
V_{SD}	source-drain voltage	$I_S = 1.2 \text{ A}; V_{GS} = 0 \text{ V}; T_j = 25 ^{\circ}\text{C}$		-	0.7	1.2	V

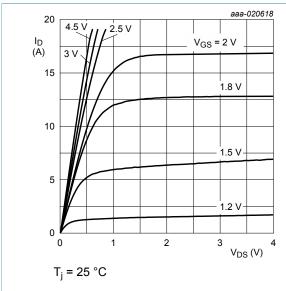


Fig. 6. Output characteristics: drain current as a function of drain-source voltage; typical values

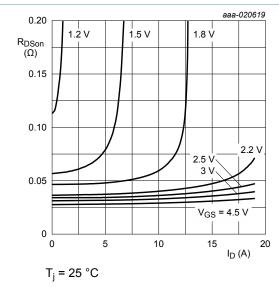


Fig. 8. Drain-source on-state resistance as a function of drain current; typical values

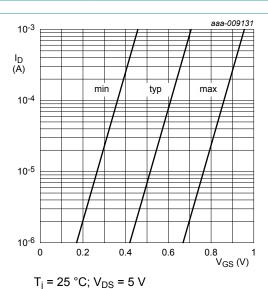


Fig. 7. Sub-threshold drain current as a function of gate-source voltage

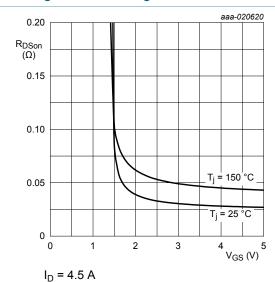


Fig. 9. Drain-source on-state resistance as a function of gate-source voltage; typical values

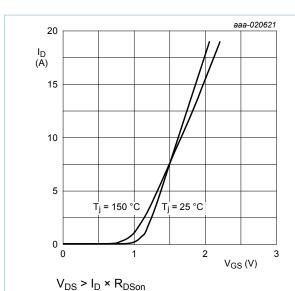


Fig. 10. Transfer characteristics: drain current as a function of gate-source voltage; typical values

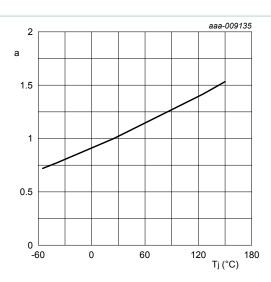


Fig. 11. Normalized drain-source on-state resistance as a function of junction temperature; typical values

$$a = \frac{R_{DSon}}{R_{DSon(25^{\circ}C)}}$$

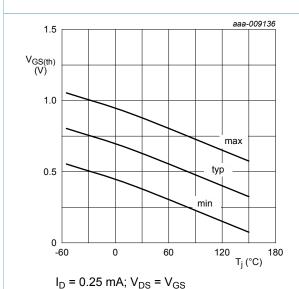
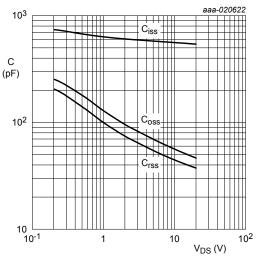


Fig. 12. Gate-source threshold voltage as a function of junction temperature



 $f = 1 MHz; V_{GS} = 0 V$

Fig. 13. Input, output and reverse transfer capacitances as a function of drain-source voltage; typical values

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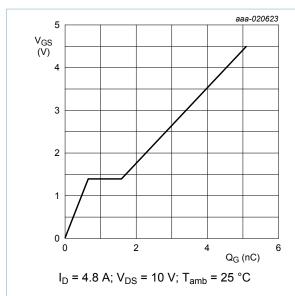


Fig. 14. Gate-source voltage as a function of gate charge; typical values

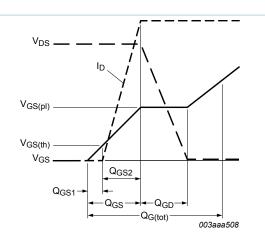


Fig. 15. MOSFET transistor: Gate charge waveform definitions

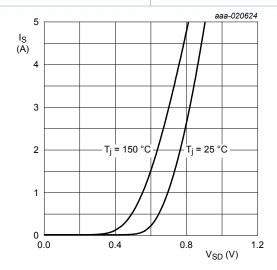
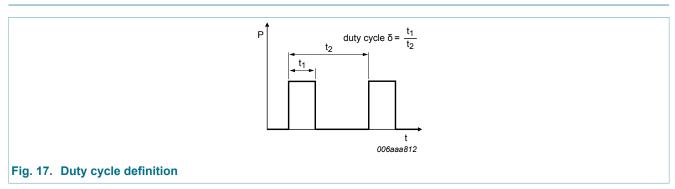


Fig. 16. Source current as a function of source-drain voltage; typical values

11. Test information

 $V_{GS} = 0 V$



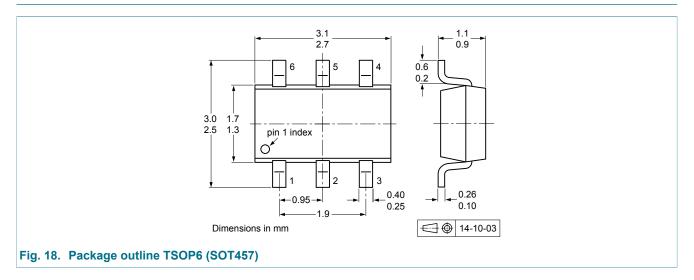
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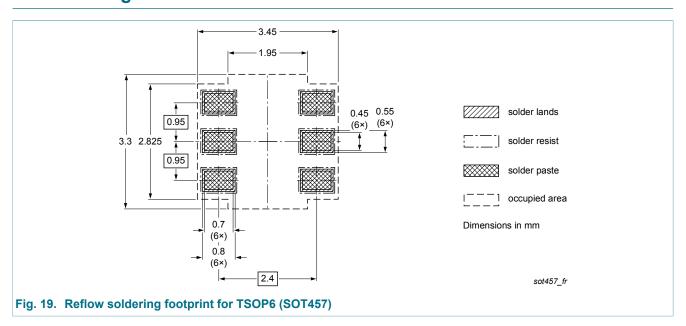
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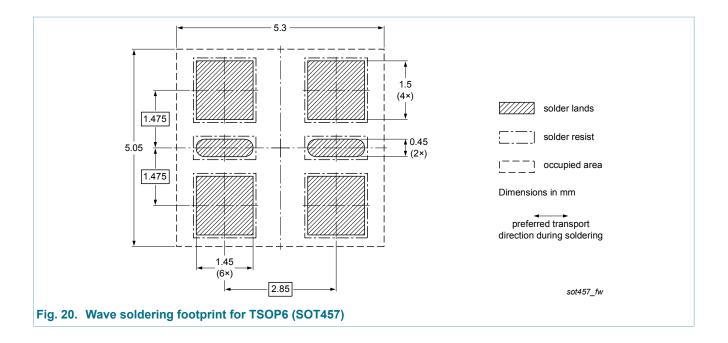
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12. Package outline



13. Soldering





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14. Revision history

Table 8. Revision history

Data sheet ID	Release date	Data sheet status	Change notice	Supersedes
PMN30UNE v.1	20160129	Product data sheet	-	-

20 V, N-channel Trench MOSFET

15. Legal information

15.1 Data sheet status

Document status [1][2]	Product status [3]	Definition
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Product [short] data sheet	Production	This document contains the product specification.

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